PREPARATION AND SOME REACTIONS OF THE COMPOUNDS $HgVsi_2$, $CdVsi_2$, AND Hg(Vsi)Br [Vsi = $(Me_3Si)_2(CH_2=CHMe_2Si)C$]. CRYSTAL STRUCTURE OF CdVsi₂

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Summary

Treatment of MBr_2 (M = Hg or Cd) with a 2 molar proportion of VsiLi [Vsi = $(Me_3Si)_2(CH_2=CHMe_2Si)C$] gave $MVsi_2$. Use of a 1 molar proportion of VsiLi in the reaction with HgBr₂ gave VsiHgBr. The $MVsi_2$ compounds are stable towards HCl in Et₂O, boiling MeCOCl containing a little LiBr, or MBr₂ in boiling THF, and CdVsi₂ is also stable towards MeOH in PhMe under reflux. HgVsi₂ reacts with CF₃CO₂H at 60°C to give Hg[C(SiMe₃)₂(SiMe₂O₂CCF₃)]₂.

An X-ray diffraction study has shown that $CdVsi_2$ has a linear structure very similar to those of $Hg[C(SiMe_3)_3]_2$ and $Mn[C(SiMe_3)_3]_2$.

Introduction

The compounds $MTsi_2$ ($Tsi = (Me_3Si)_3C$; M = Zn, Cd, or Hg) have been shown to be remarkably thermally stable (decomposing only at ca. 300°C, ca. 15°C above their melting points) and chemically resistant [1,2]. (The mercury compound is, however, readily decomposed by UV light [3].) We describe here the preparation and some properties of the related compounds $MVsi_2$ ($Vsi = (Me_3Si)_2$ -($CH_2=CHMe_2Si$)C with M = Hg and Cd, and of VsiHgBr.

Results and discussion

The reaction of $HgBr_2$ with a 2 molar proportion of VsiLi (made from VsiCl at low temperature) in THF/Et₂O/pentane (THF = tetrahydrofuran) gave HgVsi₂ (though only in 20% isolated yield). When a one molar proportion of VsiLi was used the isolated product was VsiHgBr; an attempt to determine its structure by X-ray diffraction was frustrated by considerable disorder in the crystal. Reaction of CdBr₂ with a 2 molar proportion of VsiLi gave CdVsi₂, the crystal structure of which was determined. Both HgVsi₂ and CdVsi₂ apparently undergo some decomposition at their melting points of 155 and 160°C, respectively, since the samples go black. The reasons for this marked difference in stability between the $MTsi_2$ and $MVsi_2$ species merit investigation.

Both of the MVsi₂ compounds were recovered unchanged after (i) passage of HCl for 1 h through the refluxing solutions in Et₂O and subsequent refluxing of the solutions for 1 h. (ii) boiling for 24 h with MeCOCl containing a catalytic amount of LiBr, and (iii) boiling with the corresponding MBr₂ in THF for 5 (M = Hg) or 10 h (M = Cd). No reaction took place when a solution of CdVsi₂ in 8/2 v/v PhMe/MeOH was kept at 60°C for 3 d, or when a solution of VsiHgBr in 1 M NaOMe/MeOH was kept at room temperature for 24 h or one in 20/1 v/v THF/H₂O was refluxed for 24 h.

Cleavage of the Si-vinyl bonds took place when a solution of HgVsi₂ in CF₃CO₂H was kept at 60°C; ca. 65% of the HgVsi₂ had disappeared after 4 h, and after 14 h work-up gave exclusively Hg[C(SiMe₃)₂(SiMe₂O₂CCF₃)]₂: the rate of cleavage of the Si-vinyl bonds appears to be rather similar to that for TsiSiMe₂CH=CH₂ [4]. The exclusive cleavage of the Si-vinyl bonds demonstrates the remarkable resistance to attack of the C-Hg bonds in this type of compound.

The crystal structure of CdVsi,

The molecular structure of CdVsi₂ is shown in Fig. 1, and details of bond lengths



Fig. 1. An ORTEP drawing showing the molecular structure and atom numbering. The atoms are shown as 50% thermal vibrational ellipsoids.

TABLE 1

INTRAMOLECULAR DISTANCES (Å) AND ANGLES (°) (with estimated standard deviations in parentheses)

$\overline{Cd-C(1)}$	2.172(3)	Si(1) - C(1)	1.881(3)
Si(1) - C(5)	1.864(6)	Si(1) - C(6)	1.865(6)
Si(1)-C(7)	1.879(5)	Si(2) - C(1)	1,869(4)
Si(2) - C(2)	1.854(5)	Si(2) - C(3)	1.873(6)
Si(2)-C(4)	1.869(6)	Si(3) - C(1)	1.884(4)
Si(3)-C(8)	1.876(6)	Si(3)-C(9)	1.873(5)
Si(3)-C(10)	1.879(6)	C(2)-C(11)	1.311(10)
C(1)-Si(1)-C(5)	113.3(2)	C(1)-Si(1)-C(6)	112.5(2)
C(1)-Si(1)-C(7)	112.8(2)	C(5)-Si(1)-C(6)	104.9(3)
C(5)-Si(1)-C(7)	105.7(2)	C(6)-Si(1)-C(7)	107.0(2)
C(1)-Si(2)-C(2)	110.8(2)	C(1) - Si(2) - C(3)	113.4(2)
C(1)-Si(2)-C(4)	112.8(3)	C(2)-Si(2)-C(3)	106.1(3)
C(2)-Si(2)~C(4)	106.3(2)	C(3)-Si(2)-C(4)	106.8(3)
C(1)-Si(3)-C(8)	111.8(2)	C(1) - Si(3) - C(9)	113.2(2)
C(1)-Si(3)-C(10)	113.1(2)	C(8) - Si(3) - C(9)	104.6(2)
C(8)-Si(3)-C(10)	106.9(3)	C(9) - Si(3) - C(10)	106.7(3)
Cd-C(1)-Si(1)	107.0(2)	Cd-C(1)-Si(2)	106.2(2)
Cd-C(1)-Si(3)	104.2(2)	Si(1) - C(1) - Si(2)	112.6(2)
Si(1)-C(1)-Si(3)	113.0(2)	Si(2) - C(1) - Si(3)	113.1(2)
Si(2)-C(2)-C(11)	125.0(5)		

and angles appear in Table 1. This represents the second determination of the solid-state structure of a simple diorganocadmium compound; in the first such structurally characterized species, $[Cd\{NC_5H_4C(SiMe_3)_2-2\}_2]$, however, there may be a weak interaction between Cd and N [5], as in the 4-coordinate Cd complex $[Cd(bipy)(CH_2SiMe_3)_2 \cdot 0.5 \sim bipy (bipy = 2,2'-bipyridyl)$ studied earlier [6]. Dimethylcadmium is known from Raman spectral studies to be linear in the vapour phase [7].

The two Vsi groups lie across an inversion centre, so that the coordination at Cd is strictly linear, and the two Vsi groups are fully staggered about the C-Cd-Cdirection. The Cd-C(1) distance, viz. 2.172(3) Å, is significantly longer than the Cd-C distance, 2.112(44) Å, derived spectroscopically for gaseous CdMe₂ [7], possibly a little longer than the mean Cd-C distance in the four-coordinate species $[Cd(bipy)(CH_2SiMe_1)_2] \cdot 0.5bipy$, viz. 2.14(6) [6] and significantly shorter than that in $[Cd{NC_5H_5C(SiMe_3)_2-2}_2]$, viz. 2.27 Å [5]. The structure is closely similar to those of HgTsi₂ [1] and MnTsi₂ [8], as can be seen by comparing the corresponding structural parameters listed in Table 2. The distance between the planes C(2), C(6), C(8) and C(2'), C(6'), and C(8') is ca. 3.2 Å, and so, as noted for $Mn(Tsi)_2$ (in which the corresponding distance is ca. 3.0 Å [8]), the two Vsi groups must interlock, effectively filling the space around the metal atom. The structure is also similar overall to those of the linear anions $[MTsi_2]^-$, where M = Li [9], Cu [10] or Ag [11], but there is one seemingly significant difference in detail, namely that the central Me_3Si-C bonds in the anions are apparently substantially shorter than the peripheral Si-Me bonds, (e.g. in [AgTsi₂] the mean distances are 1.83(3) and 1.90(4) Å, respectively), whereas in CdVsi₂ and MTsi₂ with M = Hg and Mn the two sets of bonds have similar lengths within the uncertainty limits. In contrast, in

TABLE 2

Parameter "	CdVsi ₂	HgTsi 2	MnTsi 2	
M-C	2.172(3)	2.142(4)	2.102(4)	
C-SiMe ₂ R	1.878(8)	1.887(4)	1.881(8)	
Si-Me	1.872(6)	1.871(3)	1.883(9)	
Si-C-Si	112.9(3)	112.5(21)	112.3(2)	
Me-Si-R	106.1(9)	106.0(12)	105.6(17)	
M-C-Si	105,8(14)	106.2(5)	106.5(8)	
C(M)-Si-R	112.9(5)	112.7(6)	113.1(16)	

MEAN BOND LENGTHS (Å) AND ANGLES (°) IN CdVsi2, HgTsi2, AND MnTsi2

^{*a*} M denotes the central metal; R = Me or $CH=CH_2$.

compounds such as $TsiSiMe_2Ph$ [12], and $TsiBPh_2$ [13], in which the presence of a fourth bulky ligand on the central carbon increases the congestion, the C-SiMe₃ bonds are longer than the Si-Me bonds; in $TsiSiMe_2Ph$ the respective mean distances are 1.915(9) and 1.876(15), and in $TsiBPh_2$ they are 1.934(3) and 1.873(6) Å.

In CdVsi₂ the strain within the Vsi groups is relieved mainly by opening of the Si-C-Si angles (mean 112.6(8)°) and closing of the Me-Si-R (R = Me or CH=CH₂) angles (mean 106.1(9)°).

Experimental

Spectra

The ¹H and ¹⁹F NMR spectra of isolated compounds refer to solutions in CCl₄, $(\delta(F)$ shifts are relative to external CFCl₃ in CDCl₃), and IR spectra to KBr discs, unless otherwise indicated. Mass spectra (electron impact) were recorded at 70 eV.

Preparation

(a) A solution of VsiLi was made by treatment of VsiCl (2.0 g, 7.2 mmol) in a mixture of THF (60 cm³) and Et₂O (8 cm³) at -100° C with n-BuLi (8.0 mmol) in pentane (5 cm³) [4], and was then added dropwise to a stirred mixture of CdBr₂ (0.96 g, 3.5 mmol) and THF (2 cm³) cooled in a bath at -80° C. The mixture was then allowed to warm to room temperature and the solvents were evaporated off under vacuum. The residue was extracted with pentane, and the extract was filtered and evaporated to leave a solid, which was recrystallized from MeOH to give CdVsi₂ (0.77 g, 18% based on VsiCl taken), m.p. 160°C (with darkening); δ (H) 0.14 (36H, s, SiMe₃), 0.21 (12H, s, SiMe₂), 5.5–6.5 (6H. m, CH=:CH₂); r(C=:C) 1585, r(Cd-C) 525, 400, 345 cm⁻¹; m/z 600 (5%, ([M]⁻), 585 (35, [M - Me]⁺), 551 (30). 357 (90, [M - Vsi]⁺), 243 (100, [Vsi]⁺), 213 (85), 169 (85), 155 (80). 141 (20), 129 (30), 85 (40, [SiMe₂CH=:CH₂]⁺), 73 (Found: C, 43.9, H, 8.4. C₂₂H₅₄CdSi₆ cale: C, 44.0; H, 9.0%).

(b) The procedure described under (a) but with HgBr₂ in place of CdBr₂ gave HgVsi₂ (20%), m.p. 155°C (with darkening); δ (H) 0.21 (36H, s, SiMe₃), 0.27 (12H, s, SiMe₂), and 5.4–6.6 (6H, m. CH=CH₂); ν (C=C) 1585 cm⁻¹, ν (Hg-C) 525, 395, 345 cm⁻¹; m/z 673 (40%, $[M - Me]^{-}$), 661 (5, $[M - CH=CH_{2}]^{-}$), 243 (100), 228 (50), 213 (100), 202 (80, [Hg]⁺), 185 (20), 169 (100), 155 (95), 129 (40), 73 (Found: C, 37.8; H, 7.9, C₂₂H₅₄HgSi₆ calc: C, 38.4; H, 7.85%).

(c) A solution of VsiLi was prepared by treatment of VsiCl (1.20 g, 4.30 mmol) in THF (40 cm³) and Et₂O (5 cm³) at -100° C with n-BuLi (4.8 mmol), then added dropwise to a stirred solution of HgBr₂ (1.73 g, 4.8 mmol) in THF (20 cm³) cooled in a bath at -80° C. The mixture was allowed to warm to room temperature during 5 h, and the solvents were removed under vacuum. The residue was extracted with pentane, and the extract was evaporated to leave VsiHgBr (0.57 g, 25%), m.p. 100°C; δ (H) 0.14 (18H, s, SiMe₃), 0.21 (6H, s, SiMe₂), and 5.5–6.55 (3H, m, CH=CH₂); ν (C=C) 1585, ν (Hg-C) 520; ν (Hg-Br) 310 cm⁻¹; m/z 526 (5%, [M]⁺), 511 (50, [M - Me]⁺), 497 (10, [$M - CH=CH_2$]⁺), 355 (20), 333 (20), 313 (20), 229 (10), 213 (10), 175 (13), 155 (162), 141 (25), 129 (10), 85 (40), 73 (100). (Found: C, 25.3; 5.8. C₁₁H₂₇BrHgSi₃ cale: C, 25.1; H, 5.7%).

Reactions

(a) A mixture of $CdVsi_2$ (0.05 g), MeOH (2 cm³), and toluene (8 cm³) was stirred at 60 °C for 3 d. The solvents were taken off under reduced pressure to leave unchanged CdVsi₂.

(b) A solution of $MVsi_2$ (M = Cd or Hg) (0.05 g) in MeCOCl (10 cm³) containing a catalytic amount of LiBr was refluxed for 24 h. Evaporation under reduced pressure left a residue which was extracted with heptane. Filtration and evaporation of the extract left unchanged MVsi₂.

(c) A solution of $MVsi_2$ (M = Cd or Hg) (0.08 mmol) and MBr₂ (0.08 mmol) in THF (10 cm³) was refluxed for 10 h then added to hexane. The organic layer was separated, washed, dried (MgSO₄), and evaporated to leave exclusively unchanged $MVsi_2$.

(d) Hydrogen chloride was bubbled for 1 h through a solution of $MVsi_2$ (0.1 mmol) in Et₂O at room temperature and the mixture then refluxed for 1 h. Evaporation followed by extraction of the residue with heptane and filtration and evaporation of the extract left only unchanged $MVsi_2$.

(1) Trifluoroacetic acid (0.5 cm³) was added to a solution of HgVsi₂ (0.14 mg, 0.02 mmol) in a drop (ca. 0.02 cm³) of CCl₄ in an NMR tube. The tube was capped then kept at 60°C. The ¹H NMR spectrum of the solution indicated that reaction was ca. 65% complete after 4 h and > 95% after 14 h. The solvent was evaporated under reduced pressure to leave a solid (0.10 mg, 55%). m.p. 85°C, which was judged to be Hg[C(SiMe₃)₂(SiMe₂O₂CCF₃)]₂; δ (H) 0.28 (36H, s, SiMe₃) and 0.59 (12H, s, SiMe₃); δ (F) -70.9 ppm; ν (C=O) 1765 cm⁻¹; m/z 844 (85%, $[M - MeH]^+$), 746 (30, $[M - CF_3CO_2H]^+$), 329 (10, $[Me_3Si)_2(CF_3CO_2Me_2Si)C]^+$), 314 (100, $[(Me_3Si)_2(CF_3CO_2Me_2Si)C - Me]^+$).

Crystal structure of CdVsi₂

A crystal, ca. $0.28 \times 0.23 \times 0.28$ mm, obtained by recrystallization from heptane, was used.

Crystal data. $C_{22}H_{54}CdSi_6$, *M* 559.6, monoclinic, *a* 9.151(1), *b* 17.730(4), *c* 10.548(2) Å, β 103.57(1)°, *U* 1663.5 Å³, *Z* 2, *D_c* 1.12 g cm⁻³, *F*(000) 636. Monochromated Mo- K_{α} radiation, λ 7.1069 Å, μ 8.74 cm⁻¹. Space group $P2_1/n$.

Data were obtained with an Enraf-Nonius CAD4 diffractometer. Preliminary cell dimensions were found by use of the SEARCH and INDEX routines of the CAD4, and final values calculated from the setting angle for 25 reflections with $\theta = 13^{\circ}$. Intensities for $hk \pm l$ reflections, with $2 < \theta < 25^{\circ}$ were measured by a

Atom	X	Ŷ	
Cd	0	0	()
Si(1)	2441(1)	345(1)	2732(1)
Si(2)	1935(1)	1544(1)	508(1)
Si(3)	583(1)	1256(1)	2012(1)
C(1)	1035(4)	847(2)	1416(3)
C(2)	761(6)	1697(3)	-1160(5)
C(3)	3826(5)	1238(5)	303(6)
C(4)	2195(7)	2492(3)	1308(6)
C(5)	1561(6)	185(3)	3887(5)
C(6)	3544(6)	376(3)	2066(5)
C(7)	3832(6)	1004(3)	3770(5)
C(8)	-1952(5)	509(3)	2238(5)
C(9)	1738(5)	1941(3)	838(5)
C(10)	29(7)	1763(4)	3613(5)
C(11)	1258(8)	1691(5)	2229(7)

FRACTIONAL ATOMIC COORDINATES ($\times 10^4$) (with estimated standard deviations in parentheses)

 $\theta/2\theta$ scan with scan width $\Delta\theta = (0.8 + 0.35\tan\theta)^\circ$. The scan rate was determined by a rapid prescan at 10 min⁻¹, and any reflection with $I < \sigma(I)$ was coded as unobserved. The remaining reflections were rescanned at such a speed as to give a minimum value of $\sigma(I)I$ of 0.05 subject to a maximum scan time of 60 s. Two standard reflections were monitored hourly but showed no significant variation. Data were corrected for Lp effects but not for absorption, and after averaging of equivalent reflections 2278 reflections with $|F^2| > \sigma(F^2)$ were used in the structure refinement. The values of $\sigma(F^2)$ were taken as $[\sigma^2(I) + (0.02I)^2]^{1/2}/Lp$.

The structure was solved by routine heavy atom methods. Refinement was by full matrix least squares with Cd, Si, and C atoms anisotropic. Hydrogen atoms were located on a difference map, and included in the refinement with a common isotropic temperature factor. The terminal hydrogen atoms of the vinyl group did not refine successfully, and were fixed at their original positions with B = 4.0 Å². Refinement converged at R = 0.032, R' = 0.042 when the maximum shift/error was 0.9 and the weighting scheme was $w = 1/\sigma^2(F)$. A final difference map was everywhere featureless.

The structure solution and refinement were carried out on a PDP11/34 computer using the Enraf–Nonius Structure Determination Package. Scattering factors for the neutral atoms were taken from ref. 14. The atom coordinates are listed in Table 3, and lists of temperature factors, hydrogen atom positions, and final structure factors are available from the authors.

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